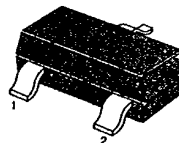


MMBC1622D8**NPN EPITAXIAL SILICON TRANSISTOR****AMPLIFIER TRANSISTOR****ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	40	V
Collector-Emitter Voltage	V_{CE0}	35	V
Emitter-Base Voltage	V_{EB0}	5.0	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	350	mW
Storage Temperature	T_{stg}	150	$^\circ\text{C}$

• Refer to MMBC1622D6 for graphs

SOT-23



1. Base 2. Emitter 3. Collector

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 25\text{V}, I_E = 0$		50	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$		50	nA
DC Current Gain	h_{FE}	$V_{CE} = 3\text{V}, I_C = 0.1\text{mA}$	150		
		$V_{CE} = 3\text{V}, I_C = 0.5\text{mA}$	450	900	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 100\text{mA}, I_B = 10\text{mA}$		0.3	V
Base-Emitter On Voltage	$V_{BE(on)}$	$I_C = 0.5\text{mA}, V_{CE} = 3\text{V}$	0.55	0.65	V
Current Gain-Bandwidth Product	f_T	$V_{CE} = 6\text{V}, I_E = 1\text{mA}$	100		MHz
		$f = 100\text{MHz}$			

Marking

